

Dual N-Channel Enhancement Mode MOSFET

■ Features

- Surface-Mounted Package
- Extremely low threshold voltage
- Advanced trench cell design
- ESD protected

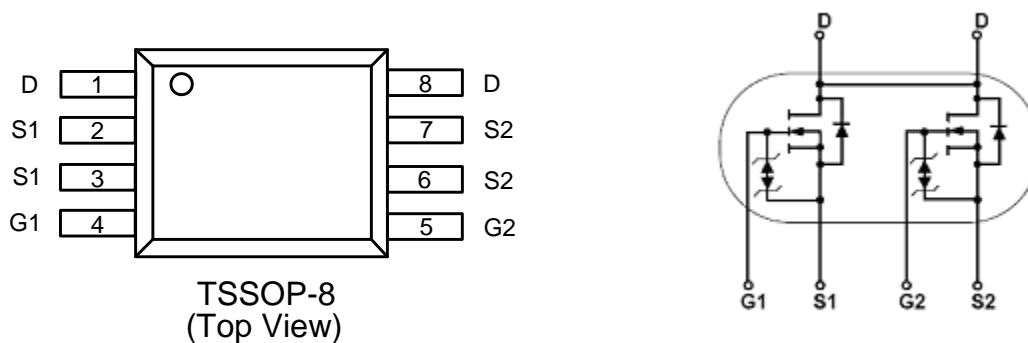
■ Package

- TSSOP-8

■ Ordering Information

Part Number	Storage Temperature	Package
LN8205CIU	-55°C to 150°C	TSSOP8

■ Pin Configuration



■ Absolute Maximum Ratings

Symbol	Parameter		Conditions	Min	Max	Unit
V_{DSS}	Drain-Source Voltage		$T_A=25^\circ\text{C}$	20		V
V_{GSS}	Gate-Source Voltage		$T_A=25^\circ\text{C}$		± 12	V
I_D	Drain Current		$T_A=25^\circ\text{C}, V_{GS}=4.5\text{V}$		6.4	A
I_{DM}	Pulsed Drain Current		$T_A=25^\circ\text{C}, V_{GS}=4.5\text{V}$		20	A
I_S	Diode Conduction		$T_A=25^\circ\text{C}$		1	A
P_{tot} *	Total Power Dissipation	TSSOP8	$T_A=25^\circ\text{C}$		1.25	W
			$T_A=100^\circ\text{C}$		0.7	W
T_J	Junction Temperature			-55	150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient				150	$^\circ\text{C/W}$

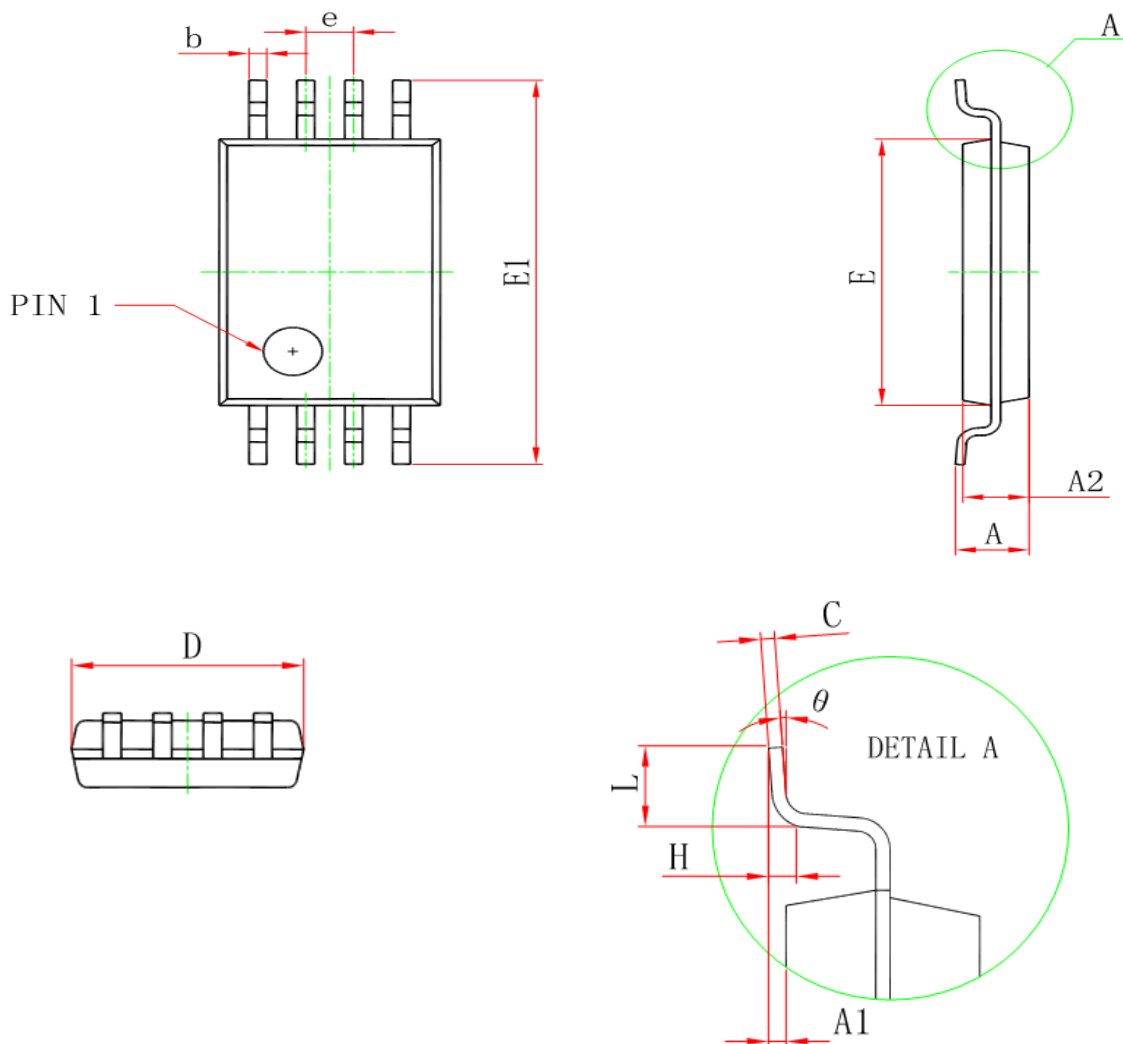
Electrical Characteristics

(TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	0.7	1.0	V
Gate-body leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 10	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS}=16V, V_{GS}=0V$			1	uA
		$V_{DS}=16V, V_{GS}=0V, T_j=85^\circ C$			30	
Drain-source on-state resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=6A$		16	20	mΩ
		$V_{GS}=2.5V, I_D=5A$		24	35	
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=1.5 A$		0.7	1.1	V
Reverse Recovery Time	tff	$I_{SD}=6.4A, dI_{SD}/dt=100A/\mu s$		27		ns
Reverse Recovery Charge	Qff			15		nc
Dynamic						
Total gate charge	Q_g	$V_{DS}=10V$ $I_D=6.4A$ $V_{GS}=4.5V$		14.5	20	nC
Gate-source charge	Q_{gs}			0.88		
Gate-drain charge	Q_{gd}			5.6		
Gate resistance	R_g	$V_{GS}=V_{DS}=0V, F=1MHz$		4		Ω
Input capacitance	C_{ISS}	$V_{DS}=10V$ $V_{GS}=0V$ $f=1MHz$		690		pF
Output capacitance	C_{OSS}			145		
Reverse transfer capacitance	C_{RSS}			140		
Turn-on delay time	$t_{D(ON)}$	$V_{DS}=10V$ $V_{GEN}=4.5V$ $I_{DS}=1A$ $R_G=6\Omega$ $R_L=10\Omega$		7	12	ns
Rise time	tr			11	24	
Turn-off delay time	$t_{D(OFF)}$			63	120	
Fall time	tf			38	65	

Package Information

- TSSOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
D	2.900	3.100	0.114	0.122
E	4.300	4.500	0.169	0.177
b	0.190	0.300	0.007	0.012
e	0.090	0.200	0.004	0.008
E1	6.250	6.550	0.246	0.258
A		1.200		0.047
A2	0.800	1.000	0.031	0.039
A1	0.050	0.150	0.002	0.006
e	0.65 (BSC)		0.026 (BSC)	
L	0.500	0.700	0.020	0.028
H	0.25 (TYP)		0.01 (TYP)	
θ	1°	7°	1°	7°